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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 20x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l100r8t6atr

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2 Description

The ultra-low-power STM32L100x6/8/B-A devices incorporate the connectivity power of the universal serial bus (USB) with the high-performance ARM® Cortex®-M3 32-bit RISC core operating at a frequency of 32 MHz (33.3 DMIPS), a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 128 Kbytes and RAM up to 16 Kbytes) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

All the devices offer a 12-bit ADC, 2 DACs and 2 ultra-low-power comparators, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

Moreover, the STM32L100x6/8/B-A devices contain standard and advanced communication interfaces: up to two I²Cs and SPIs, three USARTs and a USB.

They also include a real-time clock with sub-second counting and a set of backup registers that remain powered in Standby mode.

Finally, the integrated LCD controller has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with contrast independent of the supply voltage.

The ultra-low-power STM32L100x6/8/B-A devices operate from a 1.8 to 3.6 V power supply. They are available in the -40 to +85 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.



Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L100x6/8/B-A devices embed a nested vectored interrupt controller able to handle up to 45 maskable interrupt channels (not including the 16 interrupt lines of Cortex-M3) and 16 priority levels.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving*, higher-priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.3 Reset and supply management

3.3.1 Power supply schemes

- $V_{DD} = 1.8$ to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA} , $V_{DDA} = 1.8$ to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL.
 V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.

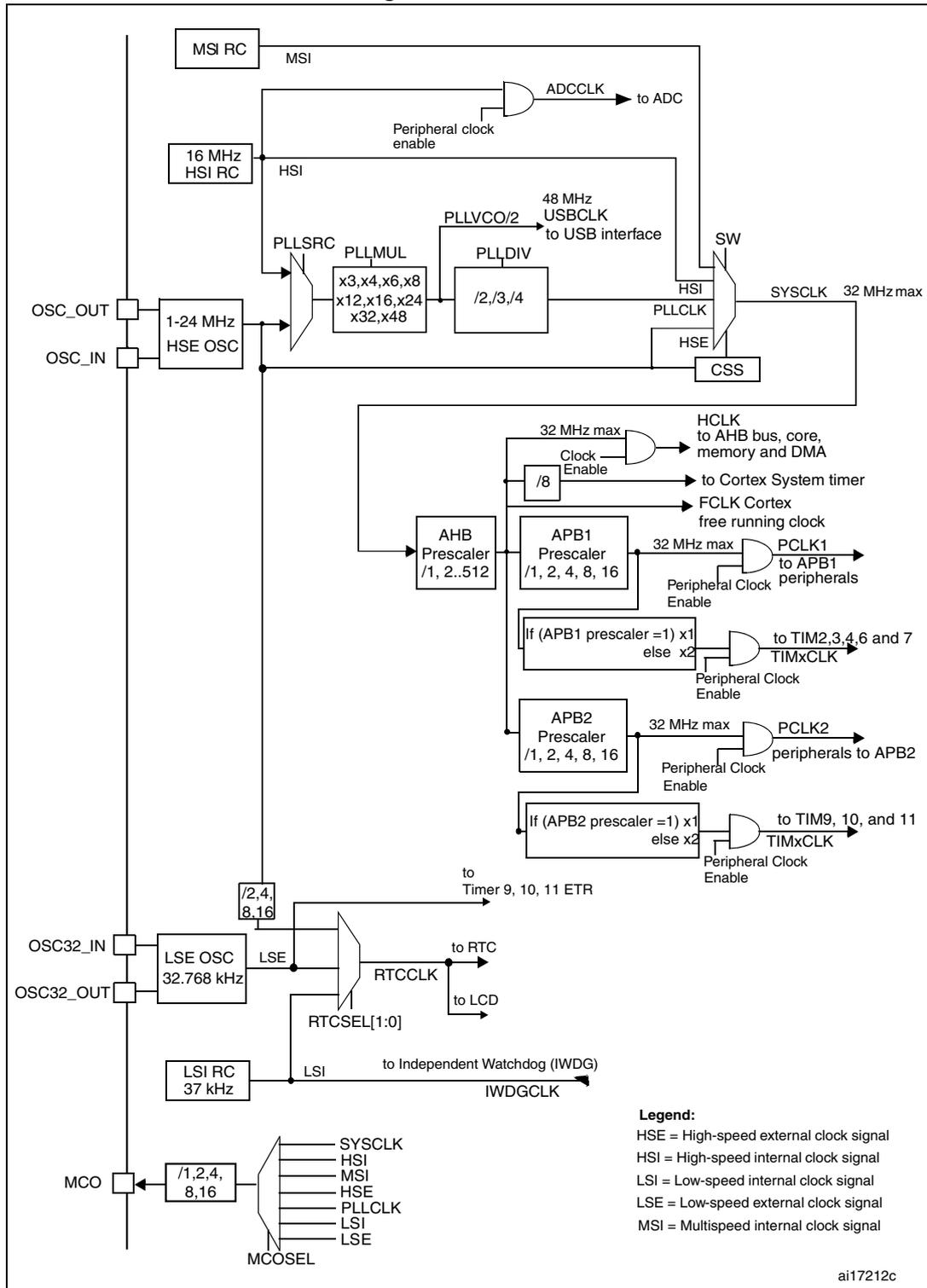
3.3.2 Power supply supervisor

The device has an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

After the V_{DD} threshold is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently.

BOR ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V.

Figure 2. Clock tree



enables accurate monitoring of the V_{DD} value. The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode see [Table 17: Embedded internal reference voltage](#).

3.11 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in non-inverting configuration.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channels' independent or simultaneous conversions
- DMA capability for each channel (including the underrun interrupt)
- external triggers for conversion

Eight DAC trigger inputs are used in the STM32L100x6/8/B-A devices. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

3.12 Ultra-low-power comparators and reference voltage

The STM32L100x6/8/B-A devices embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- one comparator with fixed threshold
- one comparator with rail-to-rail inputs, fast or slow mode. The threshold can be one of the following:
 - DAC output
 - External I/O
 - Internal reference voltage (V_{REFINT}) or V_{REFINT} submultiple (1/4, 1/2, 3/4)

Both comparators can wake up from Stop mode, and be combined into a window comparator.

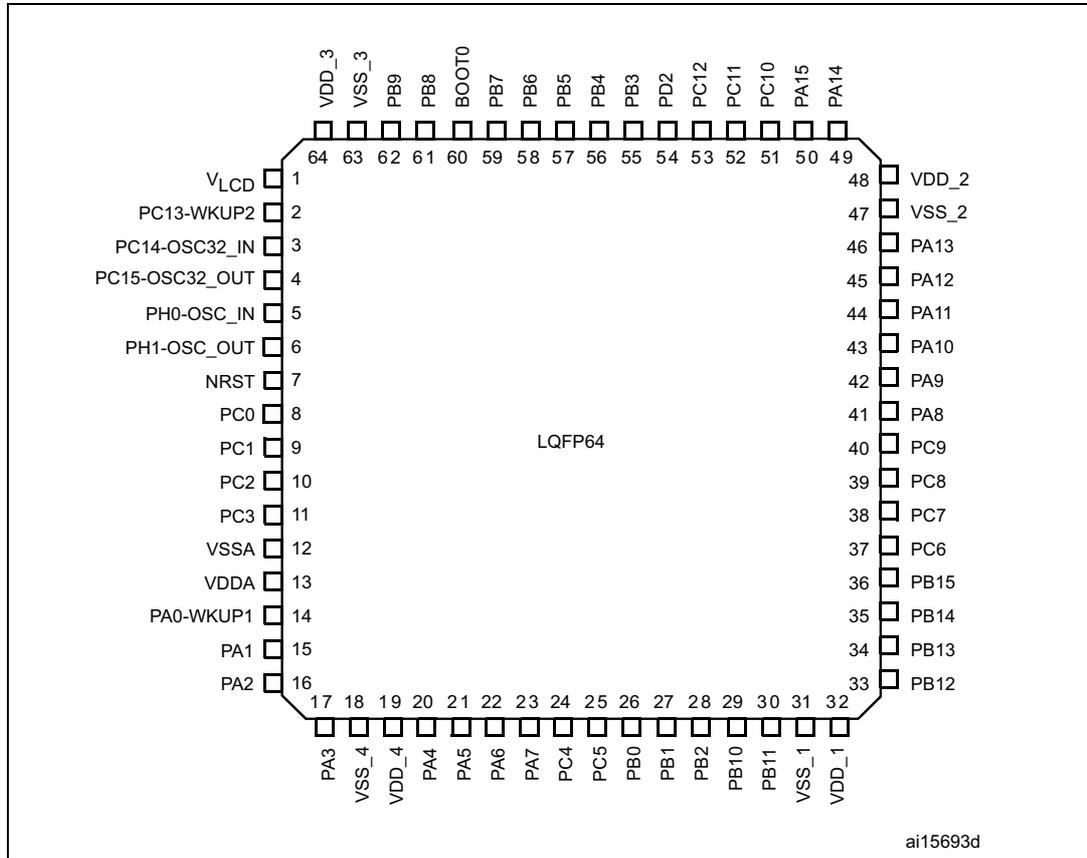
The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 μ A typical).

3.13 Routing interface

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM3 and TIM4 timer input captures. It also controls the routing of internal analog signals to ADC1, COMP1 and COMP2 and the internal reference voltage V_{REFINT} .

4 Pin descriptions

Figure 3. STM32L100RxxxA LQFP64 pinout



1. This figure shows the package top view.

Table 9. STM32L100x6/8/B-A pin definitions (continued)

Pins		Pin name	Pin type ⁽¹⁾	I/O structure	Main function ⁽²⁾ (after reset)	Pin functions	
LQFP64	UFGQFPN48					Alternate functions	Additional functions
35	27	PB14	I/O	FT	PB14	SPI2_MISO/USART3_RTS/ LCD_SEG14/TIM9_CH2	ADC_IN20/ COMP1_INP
36	28	PB15	I/O	FT	PB15	SPI2_MOSI/LCD_SEG15/ TIM11_CH1	ADC_IN21/ COMP1_INP/ RTC_REFIN
37	-	PC6	I/O	FT	PC6	TIM3_CH1/LCD_SEG24	-
38	-	PC7	I/O	FT	PC7	TIM3_CH2/LCD_SEG25	-
39	-	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26	-
40	-	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27	-
41	29	PA8	I/O	FT	PA8	USART1_CK/MCO/LCD_COM0	-
42	30	PA9	I/O	FT	PA9	USART1_TX/LCD_COM1	-
43	31	PA10	I/O	FT	PA10	USART1_RX/LCD_COM2	-
44	32	PA11	I/O	FT	PA11	USART1_CTS/SPI1_MISO	USB_DM
45	33	PA12	I/O	FT	PA12	USART1_RTS/SPI1_MOSI	USB_DP
46	34	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
47	35	V _{SS_2}	S	-	V _{SS_2}	-	-
48	36	V _{DD_2}	S	-	V _{DD_2}	-	-
49	37	PA14	I/O	FT	JTCK-SWCLK	JCTK-SWCLK	-
50	38	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/PA15/ SPI1_NSS/ LCD_SEG17/JTDI	-
51	-	PC10	I/O	FT	PC10	USART3_TX/LCD_SEG28/ LCD_SEG40/ LCD_COM4	-
52	-	PC11	I/O	FT	PC11	USART3_RX/LCD_SEG29/ LCD_SEG41/ LCD_COM5	-
53	-	PC12	I/O	FT	PC12	USART3_CK/LCD_SEG30/ LCD_SEG42/ LCD_COM6	-
54	-	PD2	I/O	FT	PD2	TIM3_ETR/LCD_SEG31/ LCD_SEG43/ LCD_COM7	-

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number														
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFOI6	AFIO7	AFI08	AFI09	AFIO11	AFIO12	AFIO13	AFIO14	AFIO15
	Alternate function														
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART1/2/3	N/A	N/A	LCD	N/A	N/A	RI	SYSTEM
PC10	-	-	-	-	-	-	-	USART3_TX	-	-	COM4 / SEG28 / SEG40	-	-	TIMx_IC3	EVENTOUT
PC11	-	-	-	-	-	-	-	USART3_RX	-	-	COM5 / SEG29 / SEG41	-	-	TIMx_IC4	EVENTOUT
PC12	-	-	-	-	-	-	-	USART3_CK	-	-	COM6 / SEG30 / SEG42	-	-	TIMx_IC1	EVENTOUT
PC13-WKUP2	-	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC2	EVENTOUT
PC14-OSC32_IN	-	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC3	EVENTOUT
PC15-OSC32_OUT	-	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC4	EVENTOUT
PD2	-	-	TIM3_ETR	-	-	-	-	-	-	-	COM7 / SEG31 / SEG43	-	-	TIMx_IC3	EVENTOUT
PH0-OSC_IN	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
PH1-OSC_OUT	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-

Table 15. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	V
		Rising edge	1.88	1.94	1.99	
V _{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V _{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V _{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V _{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V _{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V _{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
V _{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results.

Table 19. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions	f _{HCLK}	Typ	Max ⁽¹⁾	Unit			
I _{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched off	f _{HSE} = f _{HCLK} up to 16 MHz, included f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	185	255	μA		
				2 MHz	345	435			
				4 MHz	645	930			
					Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	0.755	1.5	mA
					8 MHz	1.5	2.2		
					16 MHz	3.0	3.6		
				Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	1.8	2.9		
				16 MHz	3.6	4.3			
				32 MHz	7.15	8.5			
				HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	2.95	3.7	
					Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	7.15	8.7	
				MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	39	115	μA
		MSI clock, 524 kHz	524 kHz	110		205			
		MSI clock, 4.2 MHz	4.2 MHz	690		870			

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Low-speed external user clock generated from an external source

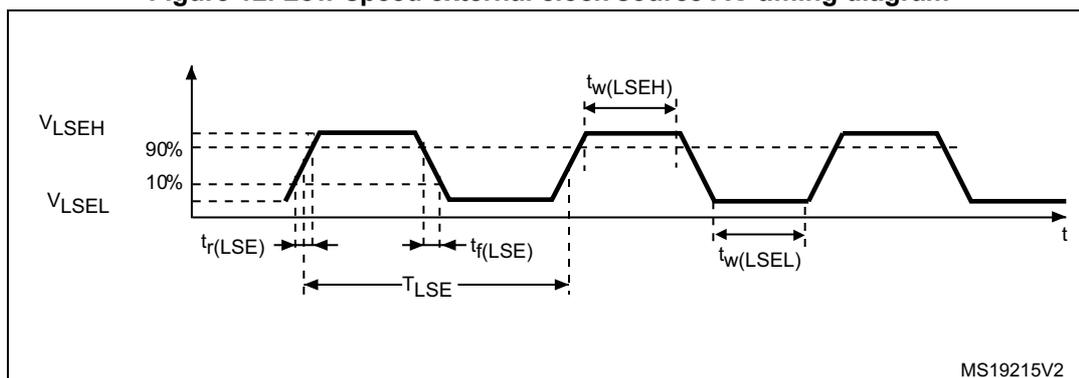
The characteristics given in the following table result from tests performed using a low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 14](#).

Table 28. Low-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	1	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage	$0.7V_{DD}$	-	V_{DD}	-
V_{LSEL}	OSC32_IN input pin low level voltage	V_{SS}	-	$0.3V_{DD}$	-
$t_{w(LSEH)}$ $t_{w(LSEL)}$	OSC32_IN high or low time	465	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time	-	-	10	
$C_{IN(LSE)}$	OSC32_IN input capacitance	-	0.6	-	pF

1. Guaranteed by design.

Figure 12. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 29](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 29. HSE oscillator characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	1		24	MHz
R_F	Feedback resistor	-		200	-	k Ω

6.3.9 Memory characteristics

The characteristics are given at $T_A = -40$ to 85 °C unless otherwise specified.

RAM memory

Table 35. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{RM}	Data retention mode ⁽¹⁾	STOP mode (or RESET)	1.8	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 36. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
V _{DD}	Operating voltage Read / Write / Erase	-	1.8	-	3.6	V
t _{prog}	Programming / erasing time for byte / word / double word / half- page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	
I _{DD}	Average current during whole program/erase operation	T _A = 25 °C, V _{DD} = 3.6 V	-	300	-	μA
	Maximum current (peak) during program/erase operation		-	1.5	2.5	mA

1. Guaranteed by design.

Table 37. Flash memory, data EEPROM endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
			Min ⁽¹⁾	Typ	Max	
N _{CYC} ⁽²⁾	Cycling (erase / write) Program memory	T _A = -40°C to 85 °C	1	-	-	kcycles
	Cycling (erase / write) EEPROM data memory		100	-	-	
t _{RET} ⁽²⁾	Data retention (program memory) after 1 kcycle at T _A = 85 °C	T _{RET} = +85 °C	10	-	-	years
	Data retention (EEPROM data memory) after 100 kcycles at T _A = 85 °C		10	-	-	

1. Guaranteed by characterization results.

2. Characterization is done according to JEDEC JESD22-A117.

SPI characteristics

Unless otherwise specified, the parameters given in the following table are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 14](#).

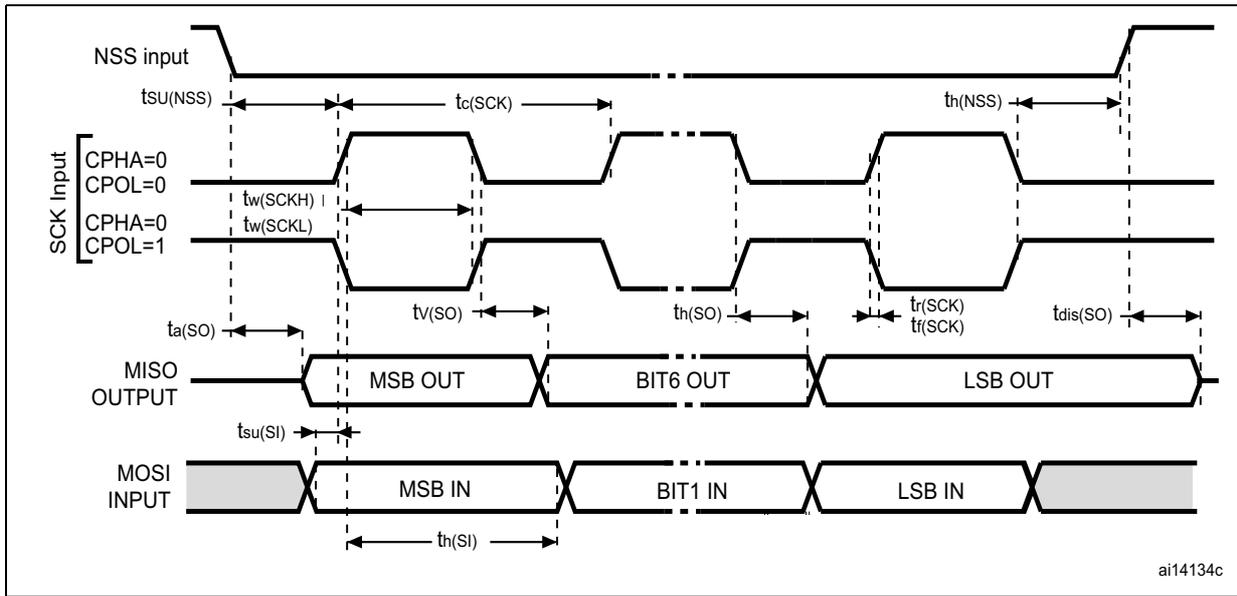
Refer to [Section 6.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 50. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	16	MHz
		Slave mode	-	16	
		Slave transmitter	-	12 ⁽³⁾	
$t_{r(SCK)}^{(2)}$ $t_{f(SCK)}^{(2)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	6	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode	$4t_{HCLK}$	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode	$2t_{HCLK}$	-	
$t_{w(SCKH)}^{(2)}$ $t_{w(SCKL)}^{(2)}$	SCK high and low time	Master mode	$t_{SCK}/2 - 5$	$t_{SCK}/2 + 3$	
$t_{su(MI)}^{(2)}$	Data input setup time	Master mode	5	-	
$t_{su(SI)}^{(2)}$		Slave mode	6	-	
$t_{h(MI)}^{(2)}$	Data input hold time	Master mode	5	-	
$t_{h(SI)}^{(2)}$		Slave mode	5	-	
$t_{a(SO)}^{(4)}$	Data output access time	Slave mode	0	$3t_{HCLK}$	
$t_{v(SO)}^{(2)}$	Data output valid time	Slave mode	-	33	
$t_{v(MO)}^{(2)}$	Data output valid time	Master mode	-	6.5	
$t_{h(SO)}^{(2)}$	Data output hold time	Slave mode	17	-	
$t_{h(MO)}^{(2)}$		Master mode	0.5	-	

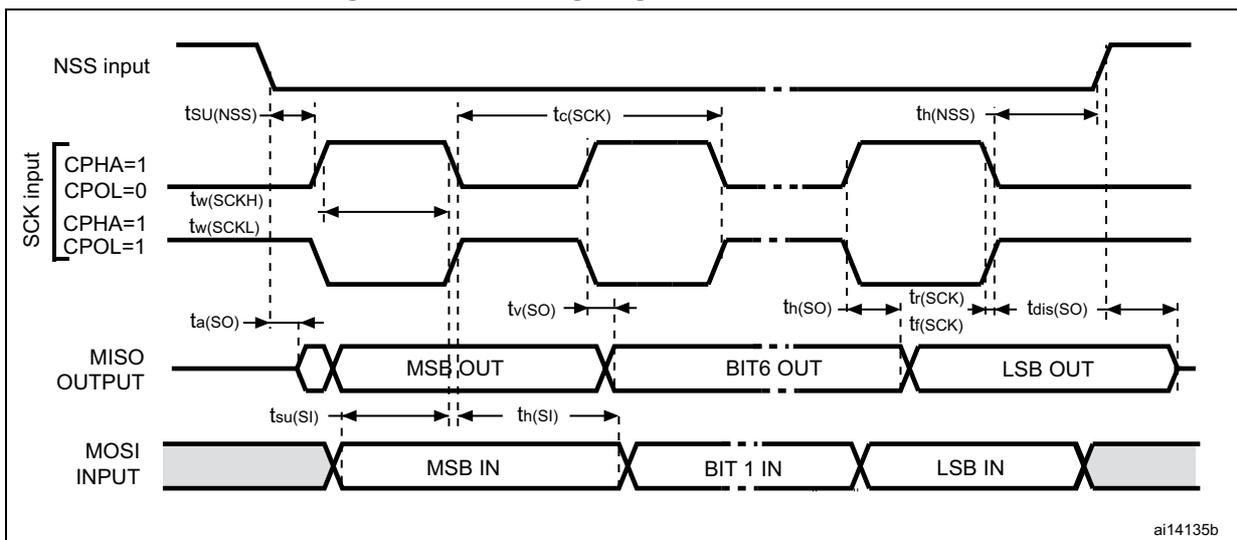
1. The characteristics above are given for voltage Range 1.
2. Guaranteed by characterization results.
3. The maximum SPI clock frequency in slave transmitter mode is given for an SPI slave input clock duty cycle (DuCy(SCK)) ranging between 40 to 60%.
4. Min time is for the minimum time to drive the output and max time is for the maximum time to validate the data.

Figure 18. SPI timing diagram - slave mode and CPHA = 0



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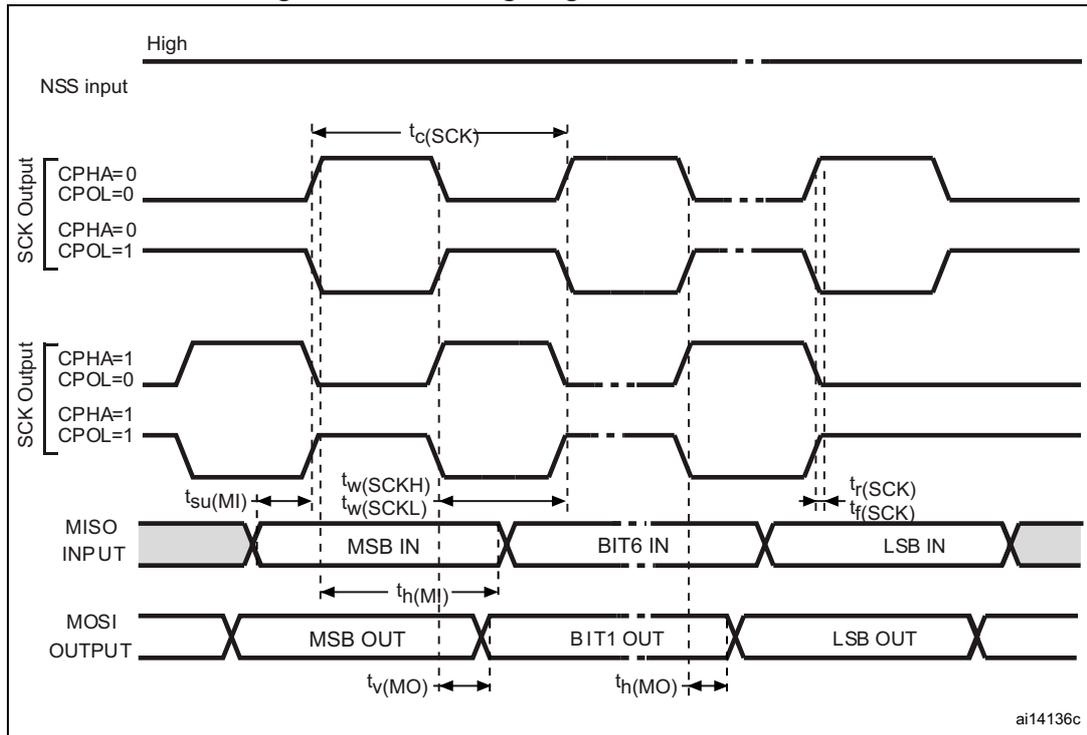
Figure 19. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾



ai14135b

1. Measurement points are done at CMOS levels: 0.3V_{DD} and 0.7V_{DD}.

Figure 20. SPI timing diagram - master mode⁽¹⁾



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

USB characteristics

The USB interface is USB-IF certified (full speed).

Table 51. USB startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}^{(1)}$	USB transceiver startup time	1	μs

1. Guaranteed by design.

- ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents. Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 6.3.12](#) does not affect the ADC accuracy.
- Guaranteed by characterization results.

Figure 22. ADC accuracy characteristics

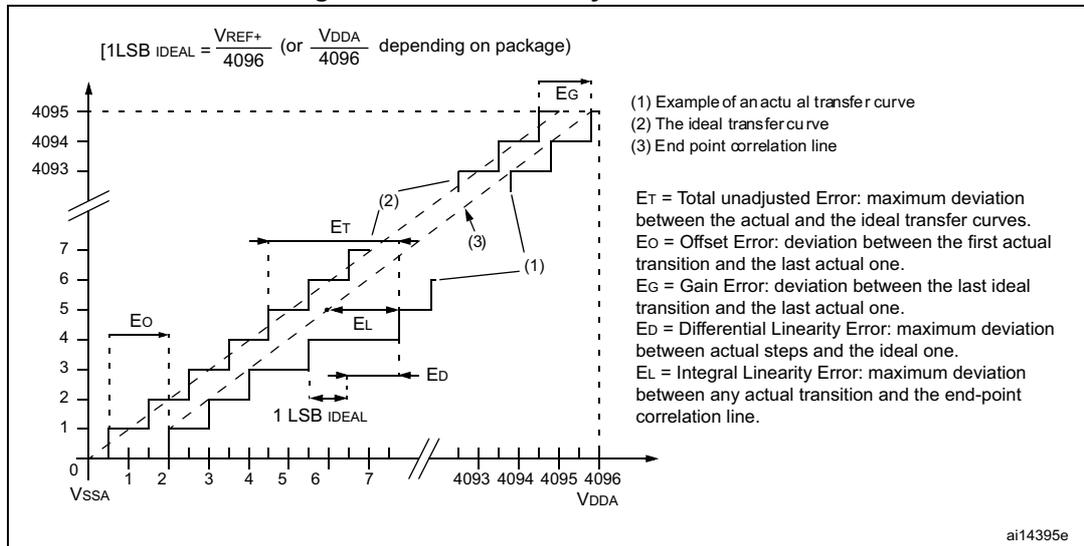
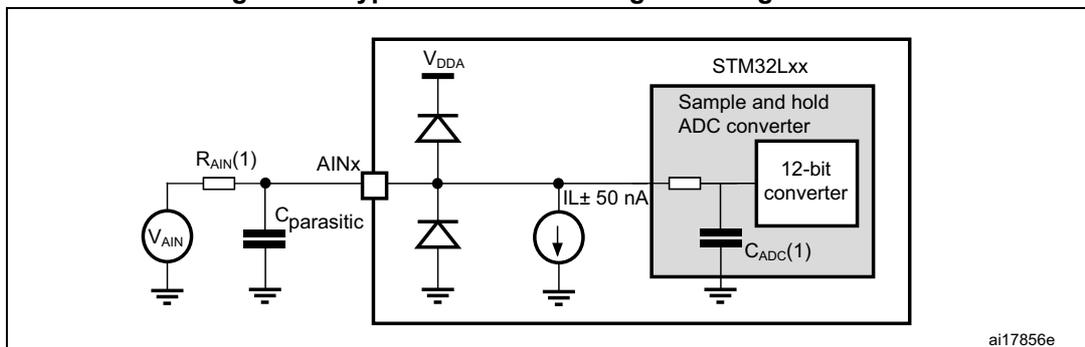


Figure 23. Typical connection diagram using the ADC



- Refer to [Table 57: Maximum source impedance \$R_{AIN\ max}\$](#) for the value of R_{AIN} and [Table 55: ADC characteristics](#) for the value of C_{ADC}
- $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

Table 58. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
dGain/dT ⁽¹⁾	Gain error temperature coefficient	V _{DDA} = 3.3V, T _A = 0 to 50 °C DAC output buffer OFF	-10	-2	0	μV/°C
		V _{DDA} = 3.3V, T _A = 0 to 50 °C DAC output buffer ON	-40	-8	0	
TUE ⁽¹⁾	Total unadjusted error	C _L ≤ 50 pF, R _L ≥ 5 kΩ DAC output buffer ON	-	12	30	LSB
		No R _L , C _L ≤ 50 pF DAC output buffer OFF	-	8	12	
t _{SETTLING}	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB)	C _L ≤ 50 pF, R _L ≥ 5 kΩ	-	7	12	μs
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	C _L ≤ 50 pF, R _L ≥ 5 kΩ	-	-	1	Msp/s
t _{WAKEUP}	Wakeup time from off state (setting the ENx bit in the DAC Control register) ⁽⁷⁾	C _L ≤ 50 pF, R _L ≥ 5 kΩ	-	9	15	μs
PSRR+	V _{DDA} supply rejection ratio (static DC measurement)	C _L ≤ 50 pF, R _L ≥ 5 kΩ	-	-60	-35	dB

1. Guaranteed by characterization results.
2. Difference between two consecutive codes - 1 LSB.
3. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
4. Difference between the value measured at Code (0x800) and the ideal value = V_{DDA}/2.
5. Difference between the value measured at Code (0x001) and the ideal value.
6. Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFFF when buffer is OFF, and from code giving 0.2 V and (V_{DDA} - 0.2) V when buffer is ON.
7. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).

Table 60. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
V _{DDA}	Analog supply voltage	-	1.8	-	3.6	V
V _{IN}	Comparator 2 input voltage range	-	0	-	V _{DDA}	V
t _{START}	Comparator startup time	Fast mode	-	15	20	μs
		Slow mode	-	20	25	
t _{d slow}	Propagation delay ⁽²⁾ in slow mode	1.8 V ≤ V _{DDA} ≤ 2.7 V	-	1.8	3.5	
		2.7 V ≤ V _{DDA} ≤ 3.6 V	-	2.5	6	
t _{d fast}	Propagation delay ⁽²⁾ in fast mode	1.8 V ≤ V _{DDA} ≤ 2.7 V	-	0.8	2	
		2.7 V ≤ V _{DDA} ≤ 3.6 V	-	1.2	4	
V _{offset}	Comparator offset error	-	-	±4	±20	mV
dThreshold/ dt	Threshold voltage temperature coefficient	V _{DDA} = 3.3V T _A = 0 to 50 °C V ₋ = V _{REFINT} , 3/4 V _{REFINT} , 1/2 V _{REFINT} , 1/4 V _{REFINT}	-	15	100	ppm /°C
I _{COMP2}	Current consumption ⁽³⁾	Fast mode	-	3.5	5	μA
		Slow mode	-	0.5	2	

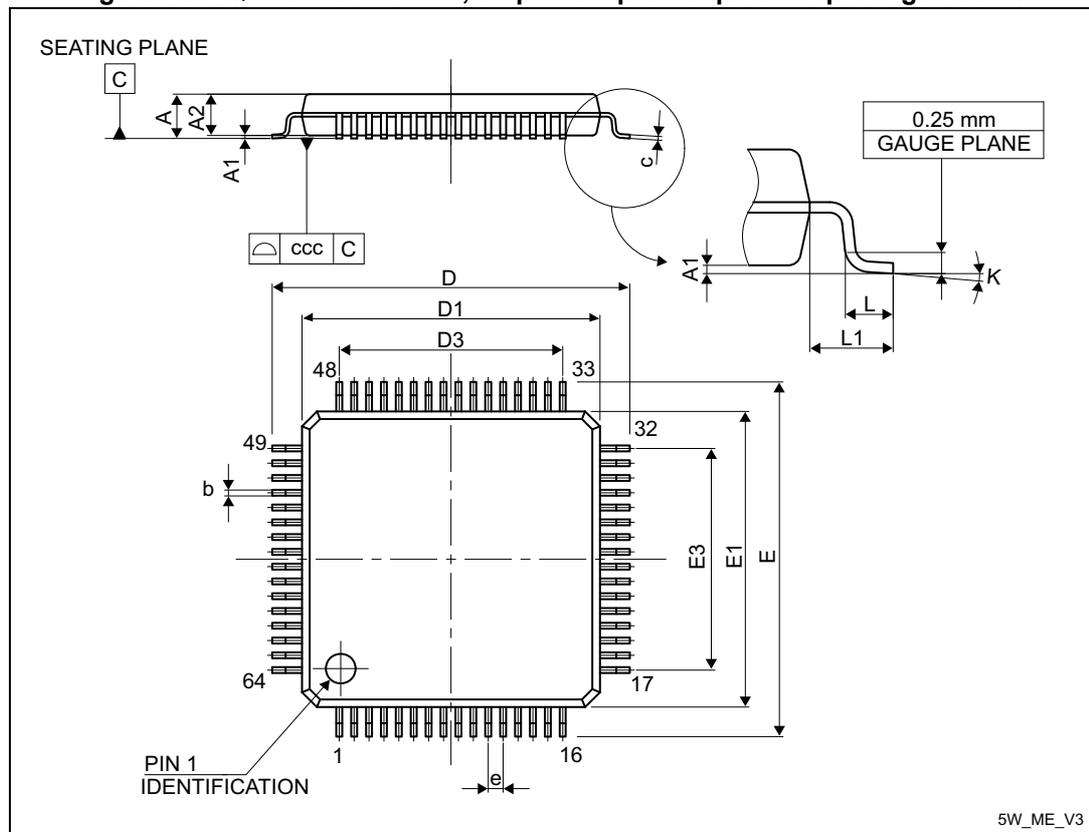
1. Guaranteed by characterization results.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage (necessary for comparator operation) is not included.

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

7.1 LQFP64 10 x 10 mm, 64-pin low-profile quad flat package information

Figure 26. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 62. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Typ	Min	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571